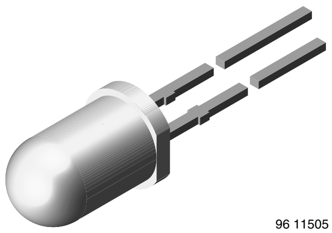
High Power Infrared Emitting Diode, RoHS Compliant, 940 nm, GaAlAs/GaAs



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DESCRIPTION

TSAL5300 is an infrared, 940 nm emitting diode in GaAlAs/GaAs technology with high radiant power molded in a blue-gray plastic package.

FEATURES

- Package type: leaded
- Package form: T-1¾
- Dimensions (in mm): ∅ 5
- Leads with stand-off
- Peak wavelength: λ_p = 940 nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: φ = ± 22°
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- Infrared remote control units with high power requirements
- Free air transmission systems
- Infrared source for optical counters and card readers

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_P (nm)	t_r (ns)
TSAL5300	45	± 22	940	800

Note
Test conditions see table “Basic Characteristics“

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSAL5300	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾
TSAL5300-MSZ	Tape and ammopack	MOQ: 5000 pcs, 1000 pcs/ammopack	T-1¾

Note
MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	t_p/T = 0.5, t_p = 100 µs	I_{FM}	200	mA
Surge forward current	t_p = 100 µs	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 5 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R_{thJA}	230	K/W

Note
T_{amb} = 25 °C, unless otherwise specified

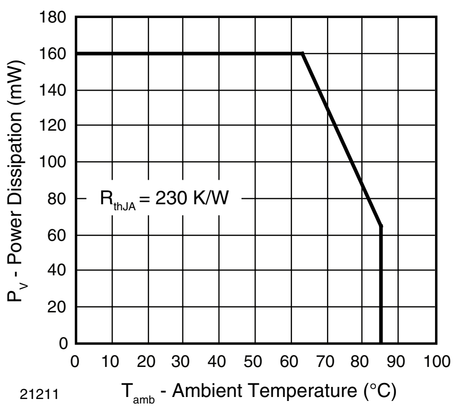

Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

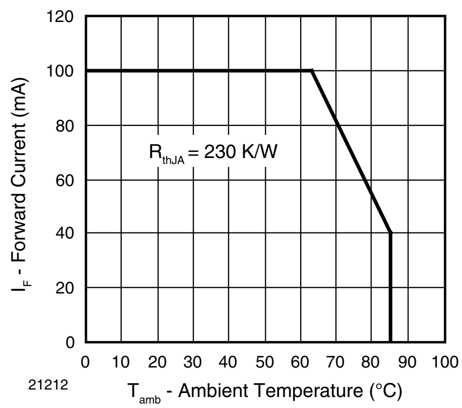

Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.35	1.6	V
	I_F = 1 A, t_p = 100 µs	V_F		2.6	3	V
Temperature coefficient of V_F	I_F = 1 mA	TK_{VF}		- 1.8		mV/K
Reverse current	V_R = 5 V	I_R			10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		25		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	30	45	150	mW/sr
	I_F = 1 A, t_p = 100 µs	I_e	260	350		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		35		mW
Temperature coefficient of ϕ_e	I_F = 20 mA	$TK\phi_e$		- 0.6		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I_F = 100 mA	λ_p		940		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		50		nm
Temperature coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.2		nm/K
Rise time	I_F = 100 mA	t_r		800		ns
	I_F = 1 A	t_r		500		ns
Fall time	I_F = 100 mA	t_f		800		ns
	I_F = 1 A	t_f		500		ns
Virtual source diameter	Method: 63 % encircled energy	d		2.3		mm

Note

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BASIC CHARACTERISTICS

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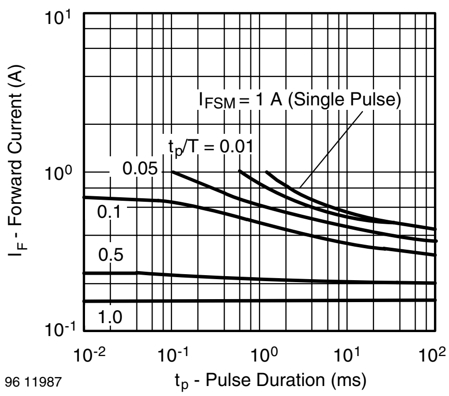


Fig. 3 - Pulse Forward Current vs. Pulse Duration

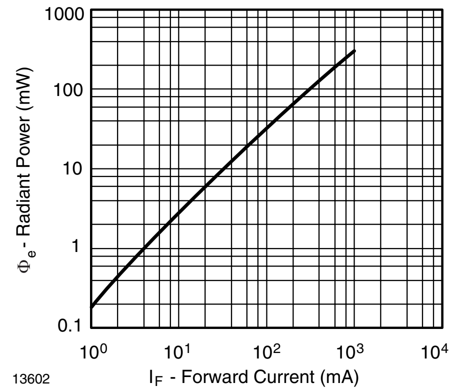


Fig. 6 - Radiant Power vs. Forward Current

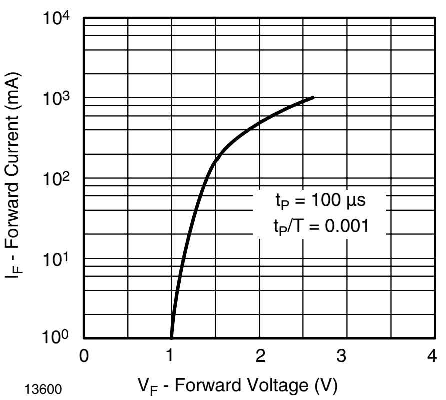


Fig. 4 - Forward Current vs. Forward Voltage

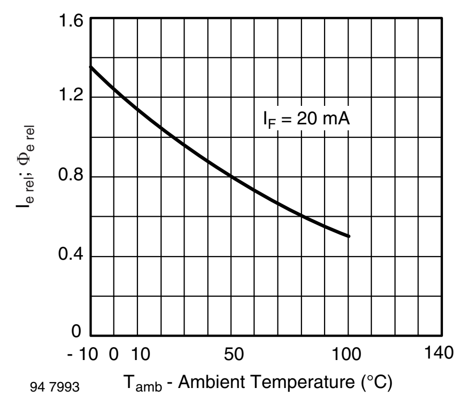


Fig. 7 - Relative Radiant Intensity/Power vs. Ambient Temperature

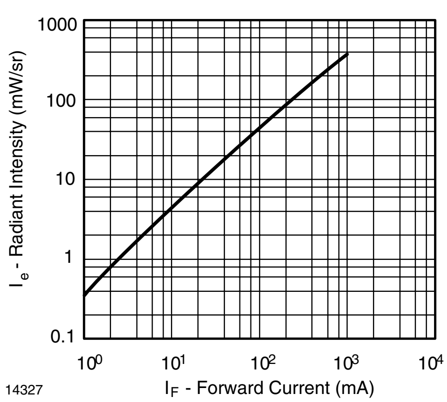


Fig. 5 - Radiant Intensity vs. Forward Current

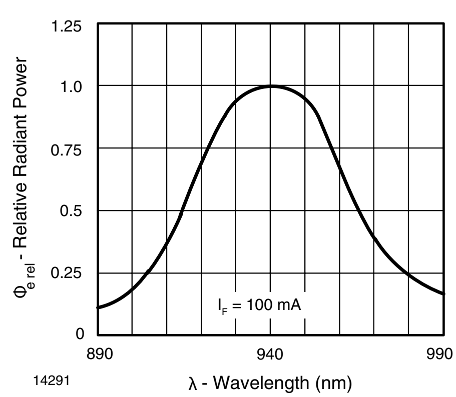


Fig. 8 - Relative Radiant Power vs. Wavelength

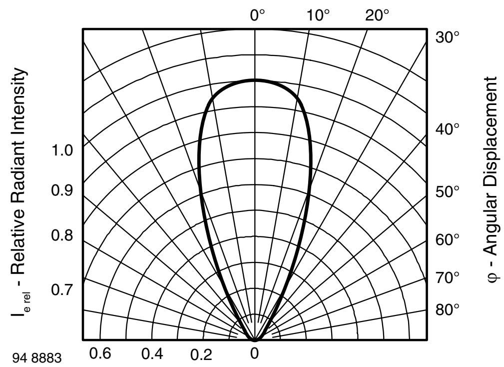
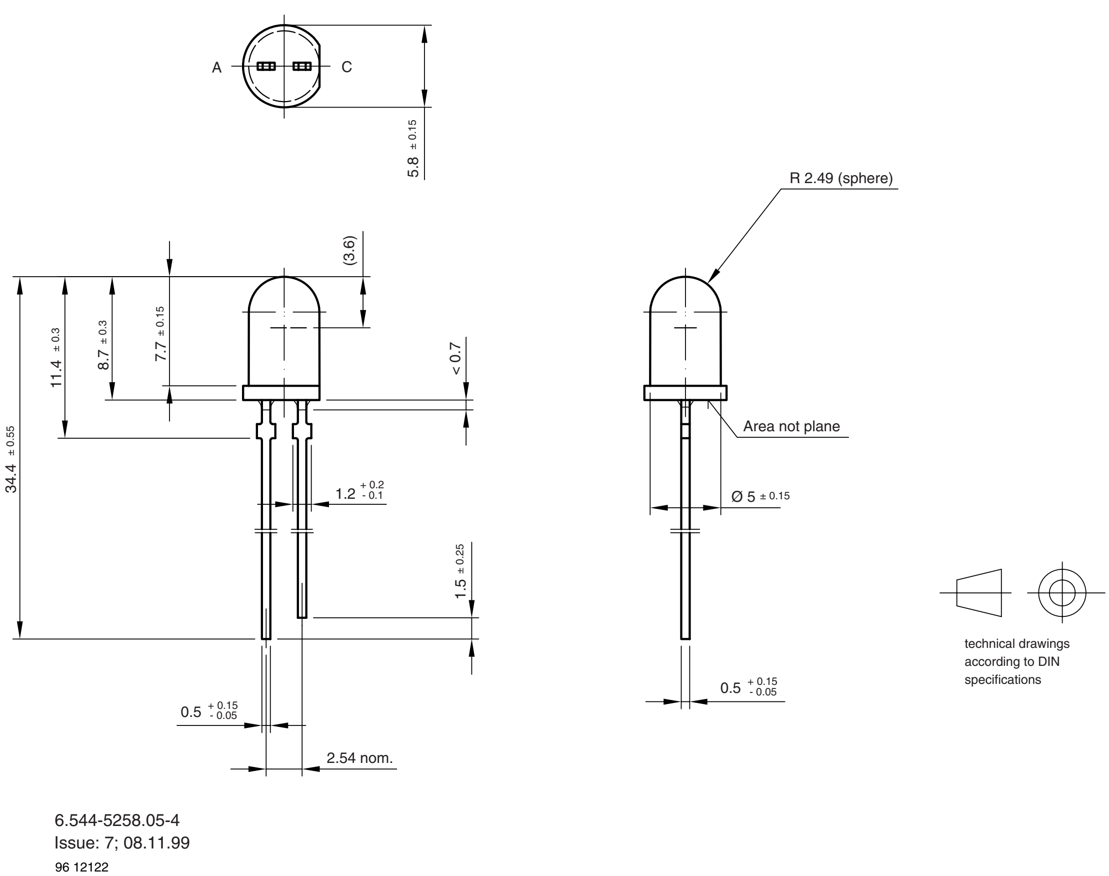


Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



TAPE DIMENSIONS TSAL5300		
OPTION	H ± 0.5 mm	QUANTITY/BOX
CS21Z	22	1000
FSZ	27	1000
GSZ	29	1000
MSZ	25.5	1000

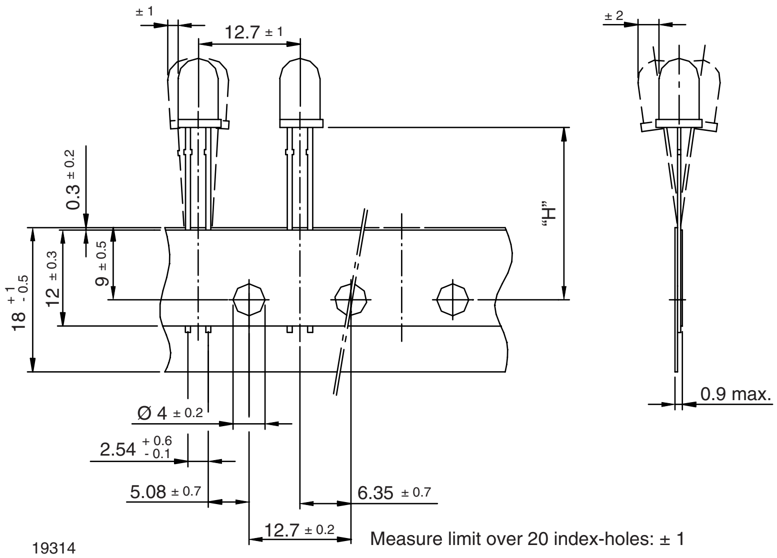


Fig. 10 - ∅ 5 mm Devices on Tape

AMMOPACK

The tape is folded in a concertina arrangement and laid in cardboard box.

If components are required with cathode before the anode (figure 12), then start of tape should be taken from the side of the box marked "-". If components are required with anode before cathode, then tape should be taken from the side of the box marked "+".

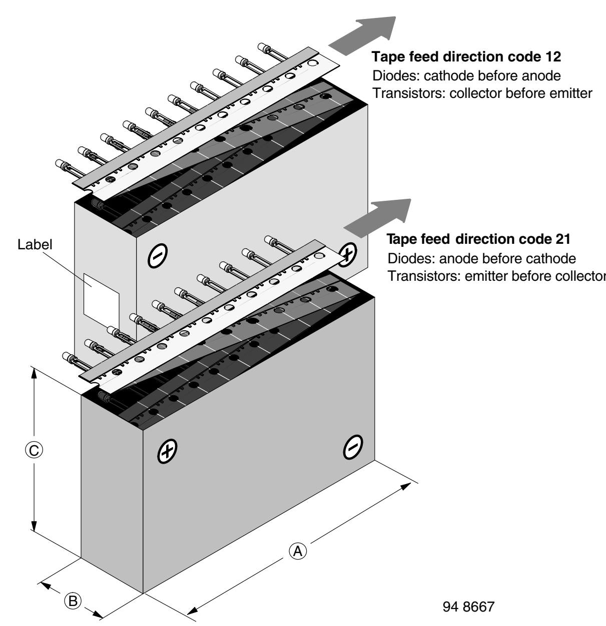


Fig. 11 - Tape Direction

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